

**AMENDMENTS TO THE CLAIMS**

1. (Cancelled)
2. (Cancelled)
3. (Cancelled)
4. (New) A method of manufacturing a semiconductor device, comprising the steps of:
  - forming a stopper film on a main surface of a semiconductor substrate;
  - forming a trench at the main surface of said semiconductor substrate using said stopper film as a mask;
  - forming an insulating film to fill said trench and to reach a level higher than said main surface and lower than an upper surface of said stopper film;
  - depositing a silicon nitride film to cover a bottom surface of a recess that is formed of a side surface of said stopper film and an upper surface of said insulating film;
  - forming an oxide-type film on said silicon nitride film covering the bottom surface of said recess; and
  - removing said stopper film using said oxide-type film as a mask.